



MDL-III-808/1~2500mW

**INFRARED DIODE LASER  
AT 808nm**





Diode infrared laser module at 808nm is made features of ultra compact, long lifetime, low cost and easy operating, which is used in measurement, communication, spectrum analysis, etc.



**SPECIFICATIONS**

Wavelength (nm)	808±3		
Output power (mW)	>1, 100, 200, 300, ..., 2500		
Transverse mode	Near TE <sub>00</sub>		
Operating mode	CW		
Power stability (rms, over 4 hours)	<1%, <3%, <5%		
Warm-up time (minutes)	<5		
M <sup>2</sup> factor	<20		
Beam divergence, full angle (mrad)	<3.0		
Dimensions of beam at the aperture (mm)	~5×8		
Beam height from base plate (mm)	24.8		
Polarization ratio	>50:1		
Pointing stability after warm-up (mrad)	<0.05		
Operating temperature (°C)	10~35		
Power supply (90-264VAC or 5VDC)	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
Modulation option	TTL/Analog 1Hz-5KHz, 1Hz-10KHz, 1Hz-30KHz, and TTL on/off		
Expected lifetime (hours)	10000		
Warranty	1 year		



MxL-III-808	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
 <p>140.8(L)×73(W)×46.2(H) mm<sup>3</sup>, 0.6kg</p>	 <p>154 (L) ×155(W) ×95 (H) mm<sup>3</sup>, 1.5kg</p>	 <p>133 (L) ×130(W) ×65 (H) mm<sup>3</sup>, 1.2kg</p>	 <p>100 (L) ×60(W) ×56 (H) mm<sup>3</sup>, 0.2kg</p>
